

SN74LV594A-Q1 汽车类 8 位并行输出串行移位寄存器

1 特性

- 符合面向汽车应用的 AEC-Q100 标准：
 - 器件温度等级 1：-40°C 至 +125°C， T_A
 - 器件 HBM ESD 分类等级 2
 - 器件 CDM ESD 分类等级 C6
- 采用可湿侧面 QFN (WBQB) 封装
- 2 V 至 5.5 V V_{CC} 运行
- 5V 时 t_{pd} 最大值为 6.5ns
- V_{OLP} (输出接地反弹) 典型值小于 0.8V ($V_{CC} = 3.3V$ 、 $T_A = 25^\circ C$ 时)
- 支持所有端口上的混合模式电压运行
- 具有存储功能的 8 位串行输入、并行输出移位寄存器
- 移位寄存器和存储寄存器上的独立直接覆盖清零
- 移位寄存器和存储寄存器的独立时钟
- 闩锁性能超过 100mA，符合 JESD 78 II 类规范

2 应用

- 输出扩展
- LED 矩阵控制
- 7 段显示控制

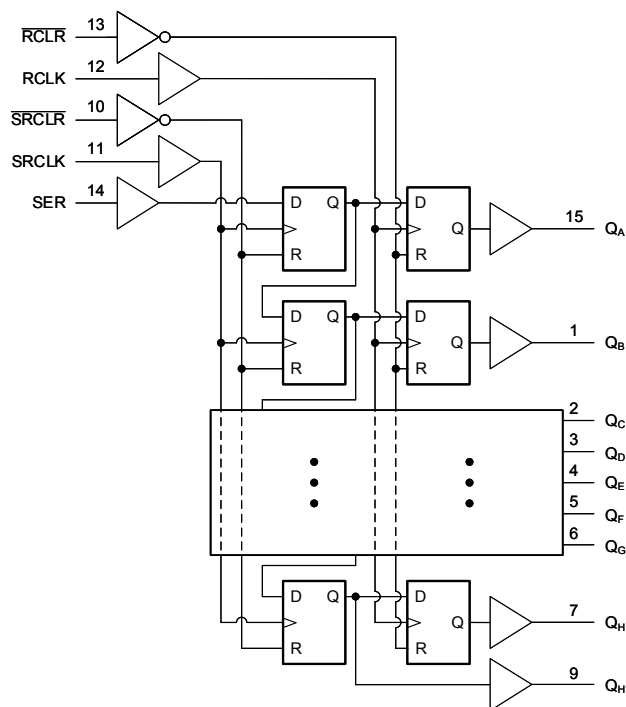
3 说明

SN74LV594A-Q1 器件是 8 位移位寄存器，可在 2V 至 5.5V V_{CC} 下运行。

封装信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
SN74LV594A-Q1	BQB (WQFN, 16)	3.60mm × 2.60mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



逻辑图 (正逻辑)



Table of Contents

1 特性	1	8 Detailed Description	12
2 应用	1	8.1 Overview.....	12
3 说明	1	8.2 Functional Block Diagram.....	12
4 Revision History	2	8.3 Feature Description.....	13
5 Pin Configuration and Functions	3	8.4 Device Functional Modes.....	13
6 Specifications	4	9 Application and Implementation	14
6.1 Absolute Maximum Ratings.....	4	9.1 Application Information.....	14
6.2 ESD Ratings.....	4	9.2 Typical Application.....	14
6.3 Recommended Operating Conditions.....	5	10 Power Supply Recommendations	16
6.4 Thermal Information.....	5	11 Layout	17
6.5 Electrical Characteristics.....	6	11.1 Layout Guidelines.....	17
6.6 Switching Characteristics: $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$	6	11.2 Layout Example.....	17
6.7 Switching Characteristics: $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$	7	12 Device and Documentation Support	18
6.8 Switching Characteristics: $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$	7	12.1 接收文档更新通知.....	18
6.9 Timing Requirements: $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$	8	12.2 支持资源.....	18
6.10 Timing Requirements: $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$	8	12.3 Trademarks.....	18
6.11 Timing Requirements: $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$	8	12.4 Electrostatic Discharge Caution.....	18
6.12 Noise Characteristics.....	9	12.5 术语表.....	18
6.13 Operating Characteristics.....	9	13 Mechanical, Packaging, and Orderable Information	18
6.14 Typical Characteristics.....	10		
7 Parameter Measurement Information	11		

4 Revision History

DATE	REVISION	NOTES
December 2022	*	Initial Release

5 Pin Configuration and Functions

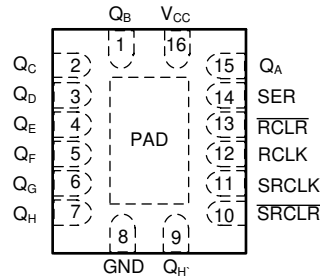


图 5-1. D, DB, or PW Package 16-Pin SOIC, SSOP, or TSSOP (Top View)

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
Q _B	1	O	Output B
Q _C	2	O	Output C
Q _D	3	O	Output D
Q _E	4	O	Output E
Q _F	5	O	Output F
Q _G	6	O	Output G
Q _H	7	O	Output H
GND	8	G	Ground pin
Q _H '	9	O	Q _H inverted
SRCLR	10	I	Serial clear
SRCLK	11	I	Serial clock
RCLK	12	I	Storage clock
RCLR	13	I	Storage clear
SER	14	I	Serial input
Q _A	15	O	Output A
V _{CC}	16	P	Power pin
Thermal Pad		-	Thermal Pad ⁽¹⁾

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	-0.5	7	V
V _I	Input voltage ⁽²⁾	-0.5	7	V
V _O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾	-0.5	7	V
V _O	Output voltage ⁽²⁾ ⁽³⁾	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		mA
I _{OK}	Output clamp current	V _O < 0		mA
I _O	Continuous output current	V _O = 0 to V _{CC}		mA
T _{stg}	Storage temperature	-65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. *Absolute Maximum Ratings* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If used outside the Recommended Operating Conditions but within the *Absolute Maximum Ratings*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The value is limited to 5.5 V maximum.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	±2000	V
		±1000	

- (1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC}	Supply voltage	2	5.5	V
V _{IH}	High-level input voltage	V _{CC} = 2 V	1.5	V
		V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7	
		V _{CC} = 3 V to 3.6 V	V _{CC} × 0.7	
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.7	
V _{IL}	Low-level input voltage	V _{CC} = 2 V	0.5	V
		V _{CC} = 2.3 V to 2.7 V	V _{CC} × 0.3	
		V _{CC} = 3 V to 3.6 V	V _{CC} × 0.3	
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.3	
V _I	Input voltage	0	5.5	V
V _O	Output voltage	0	V _{CC}	V
I _{OH}	High-level input current	V _{CC} = 2 V	-50	μA
		V _{CC} = 2.3 V to 2.7 V	-2	
		V _{CC} = 3 V to 3.6 V	6	
		V _{CC} = 4.5 V to 5.5 V	-12	
I _{OL}	Low-level output current	V _{CC} = 2 V	50	μA
		V _{CC} = 2.3 V to 2.7 V	2	
		V _{CC} = 3 V to 3.6 V	6	
		V _{CC} = 4.5 V to 5.5 V	12	
Δt/Δv	Input transition rise or fall rate	V _{CC} = 2.3 V to 2.7 V	200	ns/V
		V _{CC} = 3 V to 3.6 V	100	
		V _{CC} = 4.5 V to 5.5 V	20	
T _A	Operating free-air temperature	-40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LV594A-Q1	UNIT
		BQB (WQFN)	
		16 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	86.0	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	82.6	
R _{θJB}	Junction-to-board thermal resistance	54.9	
ψ _{JT}	Junction-to-top characterization parameter	9.5	
ψ _{JB}	Junction-to-board characterization parameter	54.9	
ψ _{JC}	Junction-to-bottom characterization parameter	32.5	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	VCC	MIN	TYP	MAX	UNIT
V _{OH}	I _{OH} = -50 μA	2 V to 5.5 V	V _{CC} - 0.1			V
	I _{OH} = -2 μA	2.3 V	2			
	I _{OH} = -6 μA	3 V	2.48			
	I _{OH} = -12 μA	4.5 V	3.8			
V _{OL}	I _{OH} = -50 μA	2 V to 5.5 V	0.1			V
	I _{OH} = -2 μA	2.3 V	0.4			
	I _{OH} = -6 μA	3 V	0.44			
	I _{OH} = -12 μA	4.5 V	0.55			
I _I	V _I = 5.5 V or GND	0 to 5.5 V	±1			μA
I _{CC}	V _I = V _{CC} or GND, I _O = 0	5.5 V	20			μA
I _{off}	V _I or V _O = 0 to 5.5 V	0	5			μA
C _i	V _I = V _{CC} or GND	3.3 V	3.5			pF

6.6 Switching Characteristics: V_{CC} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range (unless otherwise noted). See [Figure 6-1](#).

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			-40°C TO 125°C		UNIT		
				MIN	TYP	MAX	MIN	MAX			
f _{max}			C _L = 15 pF	65	80		35		MHz		
			C _L = 50 pF	60	70		30				
t _{PLH}	SRCLK	Q _A - Q _H	C _L = 15 pF		6.4	10.6	1	12.5	ns		
t _{PHL}					6.3	10.4	1	12.5			
t _{PLH}		Q _H '			7.4	12.1	1	15			
t _{PHL}					7.2	11.6	1	15			
t _{PLH}	RCLK	Q _A - Q _H			7.9	12.7	1	15.5			
t _{PHL}		Q _H '			7.4	11.9	1	15.5			
t _{PLH}	SRCLR	Q _A - Q _H		C _L = 50 pF		9.5	14.1	1		17	ns
t _{PHL}						10.8	15.5	1		19.5	
t _{PLH}		Q _H '			10.6	15.7	1	18.5			
t _{PHL}					11.3	16.1	1	20.5			
t _{PHL}	RCLR	Q _A - Q _H			12.1	17.4	1	21			
t _{PHL}		Q _H '			11.6	16.5	1	20.6			

6.7 Switching Characteristics: $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted). See [图 6-1](#).

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	$T_A = 25^\circ\text{C}$			$-40^\circ\text{C TO } 125^\circ\text{C}$		UNIT
				MIN	TYP	MAX	MIN	MAX	
f_{max}			$C_L = 15\text{ pF}$	80	120		60		MHz
			$C_L = 50\text{ pF}$	55	105		40		
t_{PLH}	SRCLK	$Q_A - Q_H$	$C_L = 15\text{ pF}$		4.6	8	1	10.5	ns
t_{PHL}					4.9	8.2	1	10.5	
t_{PLH}	RCLK	$Q_{H'}$			5.4	9.1	1	11.5	
t_{PHL}					5.5	9.2	1	11.6	
t_{PHL}	RCLK	$Q_A - Q_H$			6	9.8	1	12.1	
t_{PHL}		$Q_{H'}$			5.6	9.2	1	12	
t_{PLH}	SRCLR	$Q_A - Q_H$	$C_L = 50\text{ pF}$				1	12.5	ns
t_{PHL}							1	15	
t_{PLH}	RCLR	$Q_{H'}$					1	14	
t_{PHL}							1	15.5	
t_{PHL}	RCLR	$Q_A - Q_H$					1	16.1	
t_{PHL}		$Q_{H'}$					1	16	

6.8 Switching Characteristics: $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range (unless otherwise noted). See [图 6-1](#).

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	$T_A = 25^\circ\text{C}$			$-40^\circ\text{C TO } 125^\circ\text{C}$		UNIT
				MIN	TYP	MAX	MIN	MAX	
f_{max}			$C_L = 15\text{ pF}$	135	170		105		MHz
			$C_L = 50\text{ pF}$	120	140		85		
t_{PLH}	SRCLK	$Q_A - Q_H$	$C_L = 15\text{ pF}$		3.3	6.2	1	8	ns
t_{PHL}					3.7	6.5	1	8.5	
t_{PLH}	RCLK	$Q_{H'}$			3.7	6.8	1	8.5	
t_{PHL}					4.1	7.2	1	9	
t_{PHL}	RCLK	$Q_A - Q_H$			4.5	7.6	1	9.5	
t_{PHL}		$Q_{H'}$			4.1	7.1	1	9	
t_{PLH}	SRCLR	$Q_A - Q_H$	$C_L = 50\text{ pF}$		4.9	7.8	1	9.6	ns
t_{PHL}					5.8	8.9	1	11	
t_{PLH}	RCLR	$Q_{H'}$			5.5	8.6	1	10.5	
t_{PHL}					6	9.2	1	11.5	
t_{PHL}	RCLR	$Q_A - Q_H$			6.6	10	1	12	
t_{PHL}		$Q_{H'}$			6	9.2	1	11.5	

6.9 Timing Requirements: $V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

over recommended operating free-air temperature range. See [图 6-1](#).

		$T_A = 25^\circ\text{C}$		$-40^\circ\text{C TO } 125^\circ\text{C}$		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	RCLK or SRCLK high or low		8.5		ns
		RCKR or SCRCLR low		7.5		
t_{su}	Setup time	SER before SRCLK \uparrow		6		ns
		SRCLK \uparrow before RCLK \uparrow		10		
		SCRCLR low before RCLK \uparrow ⁽¹⁾		10.5		
		SRCLR high (inactive) before SRCLK \uparrow		7.5		
		RCLK high (inactive) before RCLK \uparrow		8.5		
t_h	Hold time	SER after SRCLK \uparrow		2		ns

(1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

6.10 Timing Requirements: $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$

over recommended operating free-air temperature range. See [图 6-1](#).

		$T_A = 25^\circ\text{C}$		$-40^\circ\text{C TO } 125^\circ\text{C}$		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	RCLK or SRCLK high or low		6.5		ns
		RCKR or SCRCLR low		6		
t_{su}	Setup time	SER before SRCLK \uparrow		4		ns
		SRCLK \uparrow before RCLK \uparrow		9.5		
		SCRCLR low before RCLK \uparrow ⁽¹⁾		10		
		SRCLR high (inactive) before SRCLK \uparrow		5.5		
		RCLK high (inactive) before RCLK \uparrow		6		
t_h	Hold time	SER after SRCLK \uparrow		2		ns

(1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

6.11 Timing Requirements: $V_{CC} = 5\text{ V} \pm 0.5\text{ V}$

over recommended operating free-air temperature range. See [图 6-1](#).

		$T_A = 25^\circ\text{C}$		$-40^\circ\text{C TO } 125^\circ\text{C}$		UNIT
		MIN	MAX	MIN	MAX	
t_w	Pulse duration	RCLK or SRCLK high or low		6		ns
		RCKR or SCRCLR low		6.2		
t_{su}	Setup time	SER before SRCLK \uparrow		3.5		ns
		SRCLK \uparrow before RCLK \uparrow		6		
		SCRCLR low before RCLK \uparrow ⁽¹⁾		5.5		
		SRCLR high (inactive) before SRCLK \uparrow		4		
		RCLK high (inactive) before RCLK \uparrow		4.5		
t_h	Hold time	SER after SRCLK \uparrow		2.5		ns

(1) This setup time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.

6.12 Noise Characteristics

over operating free-air temperature range (unless otherwise noted), $V_{CC} = 3.3\text{ V}$, $C_L = 50\text{ pF}$, $T_A = 25^\circ\text{C}^{(1)}$

PARAMETER		MIN	TYP	MAX	UNIT
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.5	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		-0.1	-0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		2.8		V
$V_{IH(V)}$	High-level dynamic input voltage	2.31			V
$V_{IL(V)}$	Low-level dynamic input voltage			0.99	V

(1) Characteristics are for surface-mount packages only.

6.13 Operating Characteristics

$T_A = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	$f = 10\text{ MHz}$	3.3 V	93	pF
			5 V	112	

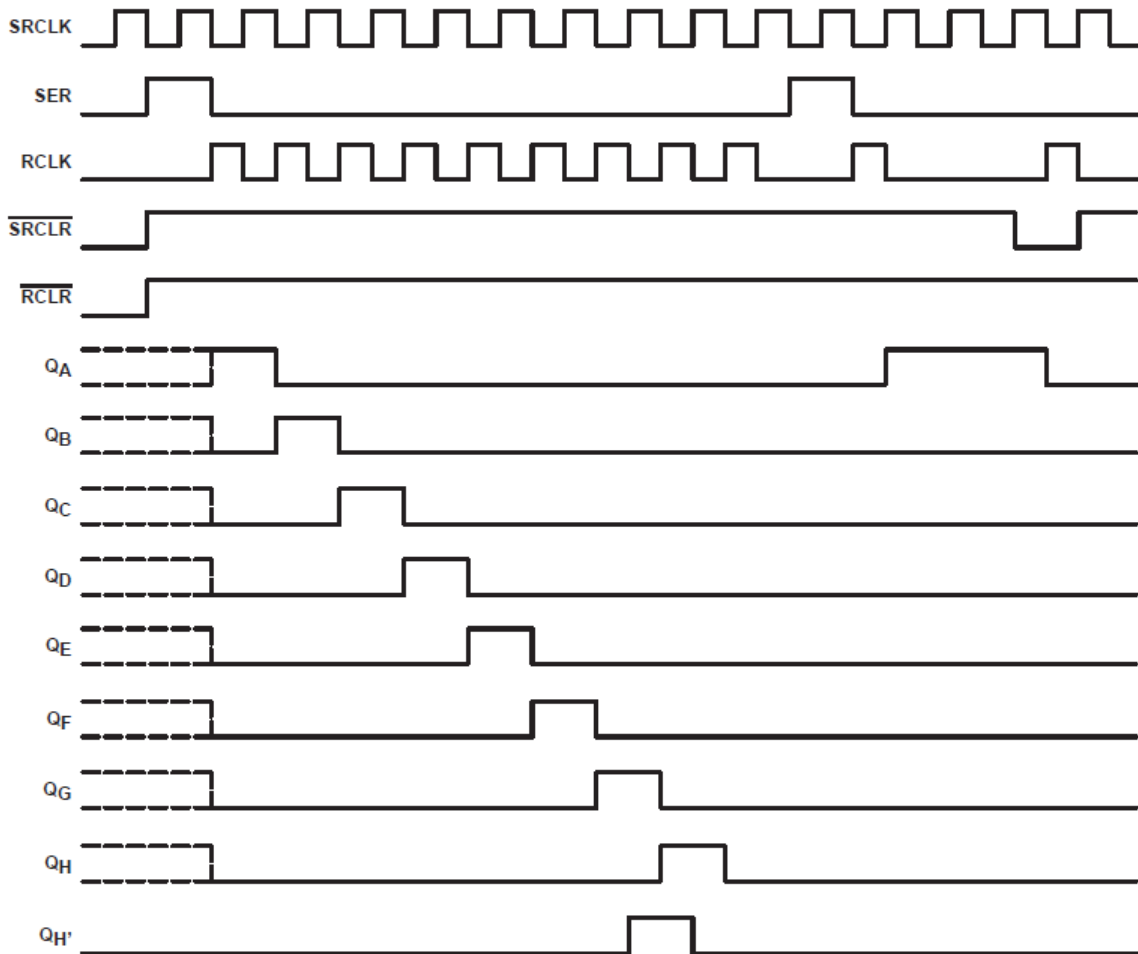
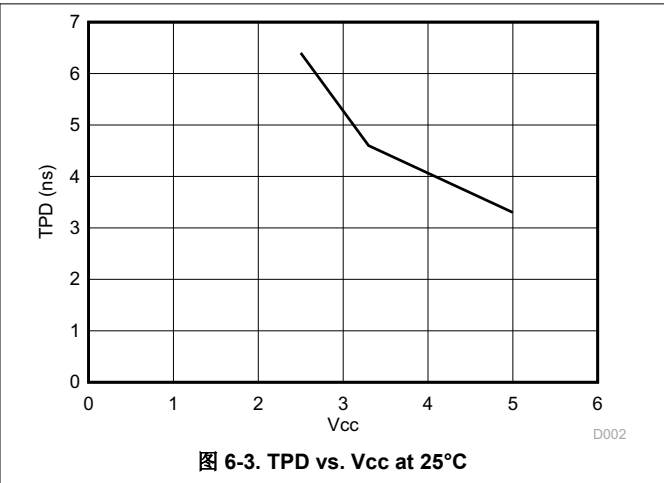
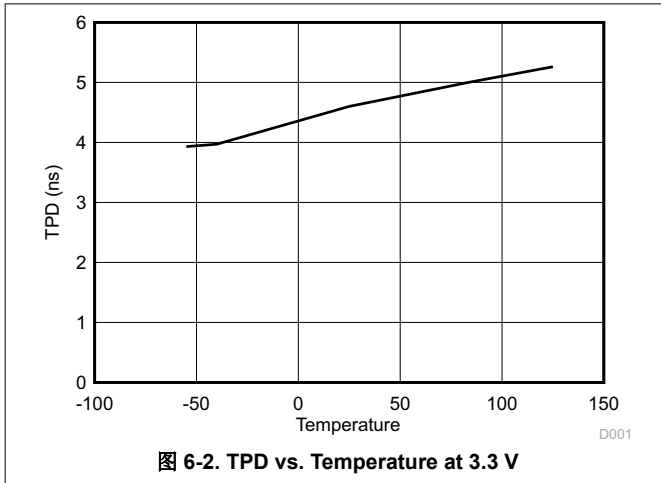
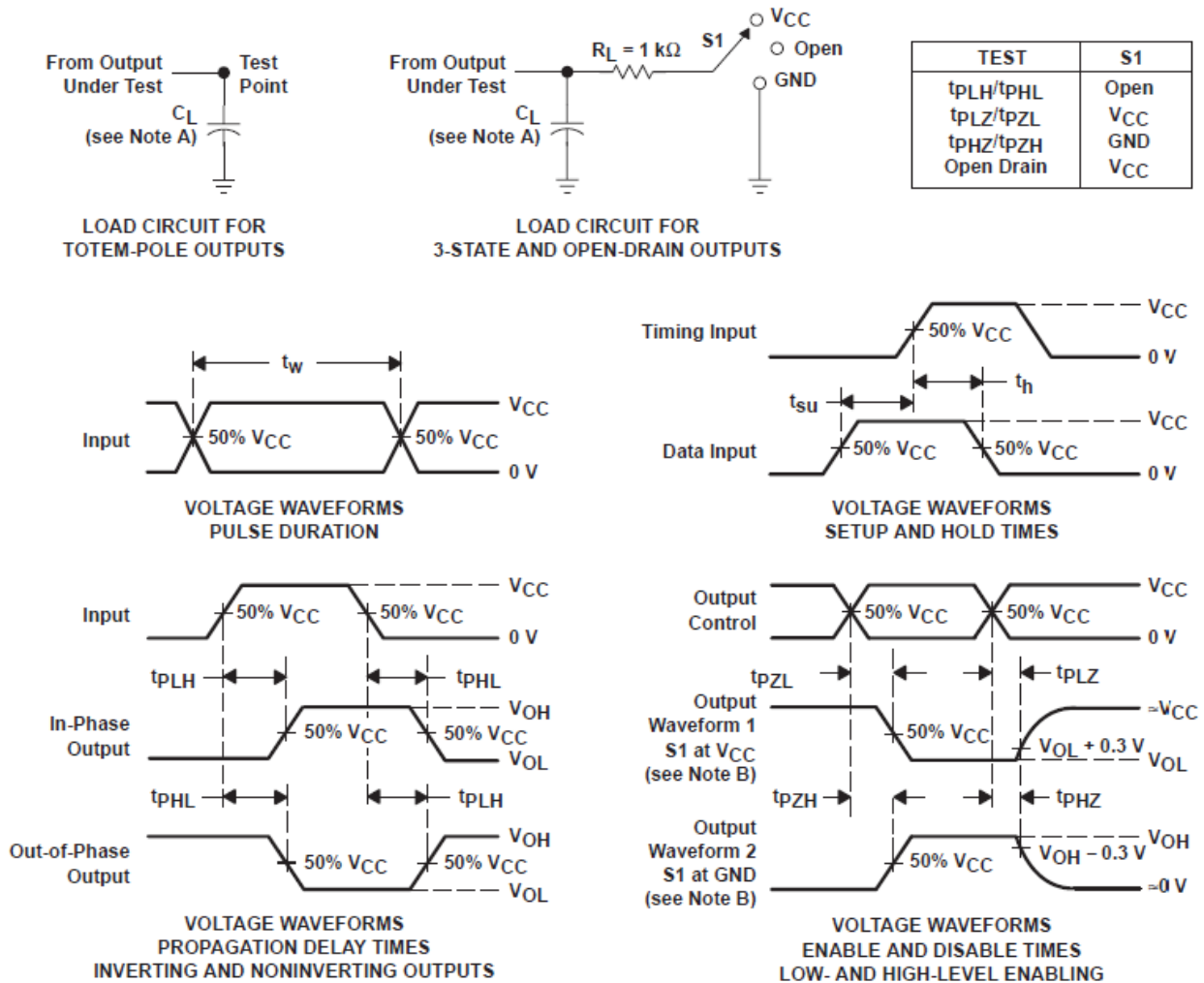


图 6-1. Timing Diagram

6.14 Typical Characteristics



7 Parameter Measurement Information



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1\text{ MHz}$, $Z_O = 50\ \Omega$, $t_r \leq 3\text{ ns}$, $t_f \leq 3\text{ ns}$.
 - D. The outputs are measured one at a time, with one input transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PHL} and t_{PLH} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

图 7-1. Load Circuit and Voltage Waveforms

8.3 Feature Description

The device's wide operating range allows it to be used in a variety of systems that use different logic levels. The low propagation delay allows fast switching and higher speeds of operation. In addition, the low ground bounce stabilizes the performance of non-switching outputs while another output is switching.

8.4 Device Functional Modes

表 8-1. Function Table

INPUTS					FUNCTION
SER	SRCLK	SRCLR	RCLK	RCLR	
X	X	L	X	X	Shift register is cleared.
L	↑	H	X	X	First stage of shift register goes low. Other stages store the data of previous stage, respectively.
H	↑	H	X	X	First stage of shift register goes high. Other stages store the data of previous stage, respectively.
L	↓	H	X	X	Shift register state is not changed.
X	X	X	X	L	Storage register is cleared.
X	X	X	↑	H	Shift register data is stored in the storage register.
X	X	X	↓	H	Storage register state is not changed.

9 Application and Implementation

备注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74LV594A-Q1 is a low drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs.

9.2 Typical Application

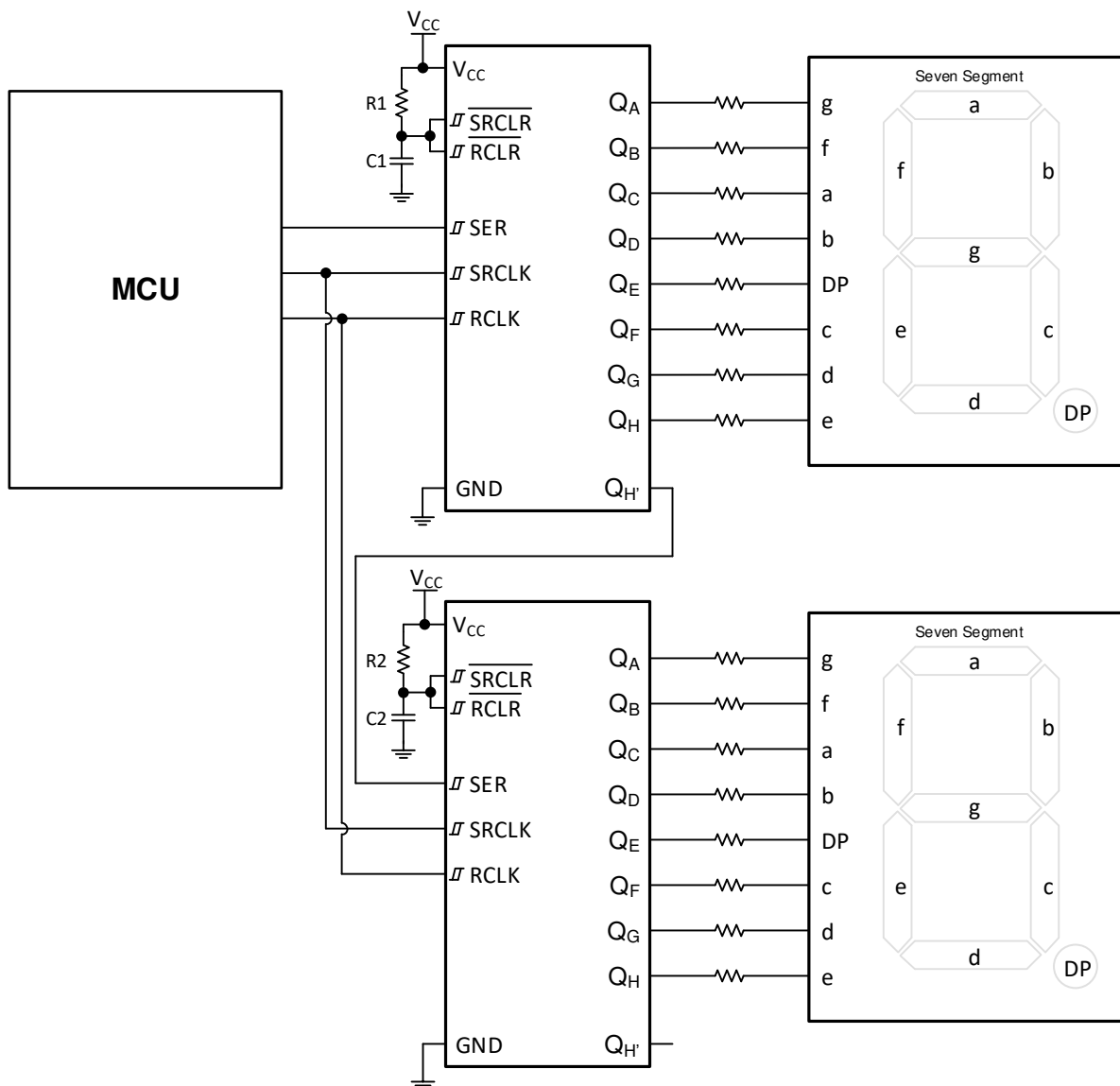


图 9-1. Typical Application Schematic

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so consider routing and load conditions to prevent ringing.

9.2.2 Detailed Design Procedure

- Recommended input conditions:
 - Rise time and fall time specs. See $(\Delta t / \Delta V)$ in [§ 6.3](#).
 - Specified high and low levels. See $(V_{IH}$ and $V_{IL})$ in [§ 6.3](#).
 - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC} .
- Recommended output conditions:
 - Load currents should not exceed 25 mA per output and 50 mA total for the part.
 - Outputs should not be pulled above V_{CC} .

9.2.3 Application Curves

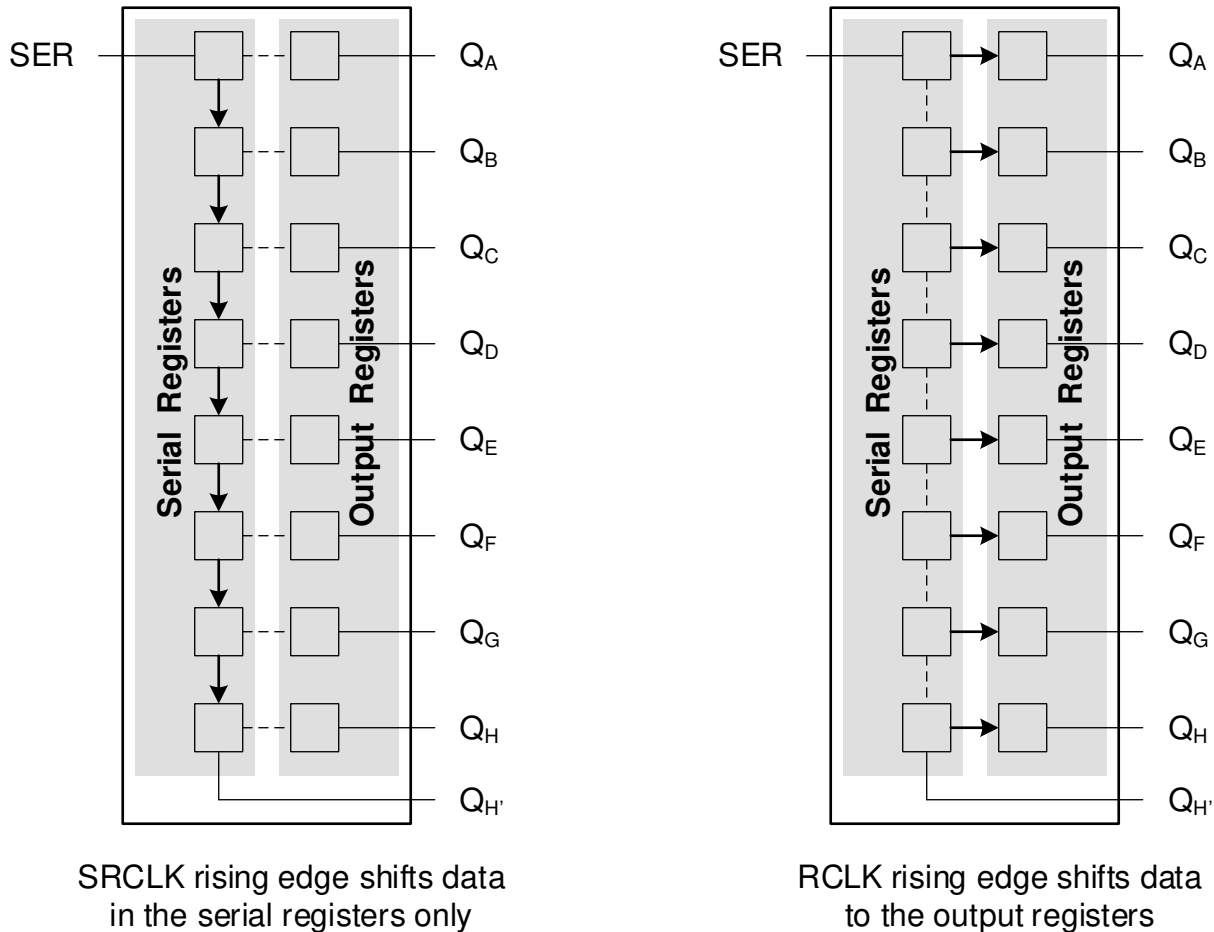


图 9-2. Simplified functional diagram showing clock operation

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the [Recommended Operating Conditions](#). Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, TI recommends a 0.1- μ F capacitor and if there are multiple V_{CC} terminals then TI recommends a 0.01- μ F or 0.022- μ F capacitor for each power terminal. Multiple bypass capacitors can be paralleled to reject different frequencies of noise. Frequencies of 0.1 μ F and 1 μ F are commonly used in parallel. The bypass capacitor should be installed as close as possible to the power terminal for best results.

11 Layout

11.1 Layout Guidelines

When using multiple bit logic devices inputs should not ever float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only three of the four buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Specified below are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC} whichever make more sense or is more convenient. Floating outputs is generally acceptable, unless the part is a transceiver. If the transceiver has an output enable pin, then it will disable the outputs section of the part when asserted. This will not disable the input section of the I.O' s so they also cannot float when disabled.

11.2 Layout Example

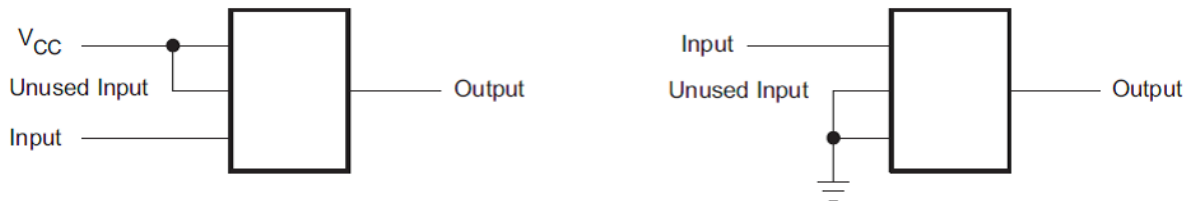


图 11-1. Layout Example

12 Device and Documentation Support

12.1 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](https://www.ti.com) 上的器件产品文件夹。点击 [订阅更新](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.2 支持资源

TI E2E™ 支持论坛 是工程师的重要参考资料，可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题可获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《[使用条款](#)》。

12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

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12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV594AQWBQBRQ1	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LV594Q	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LV594A-Q1 :

- Catalog : [SN74LV594A](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

GENERIC PACKAGE VIEW

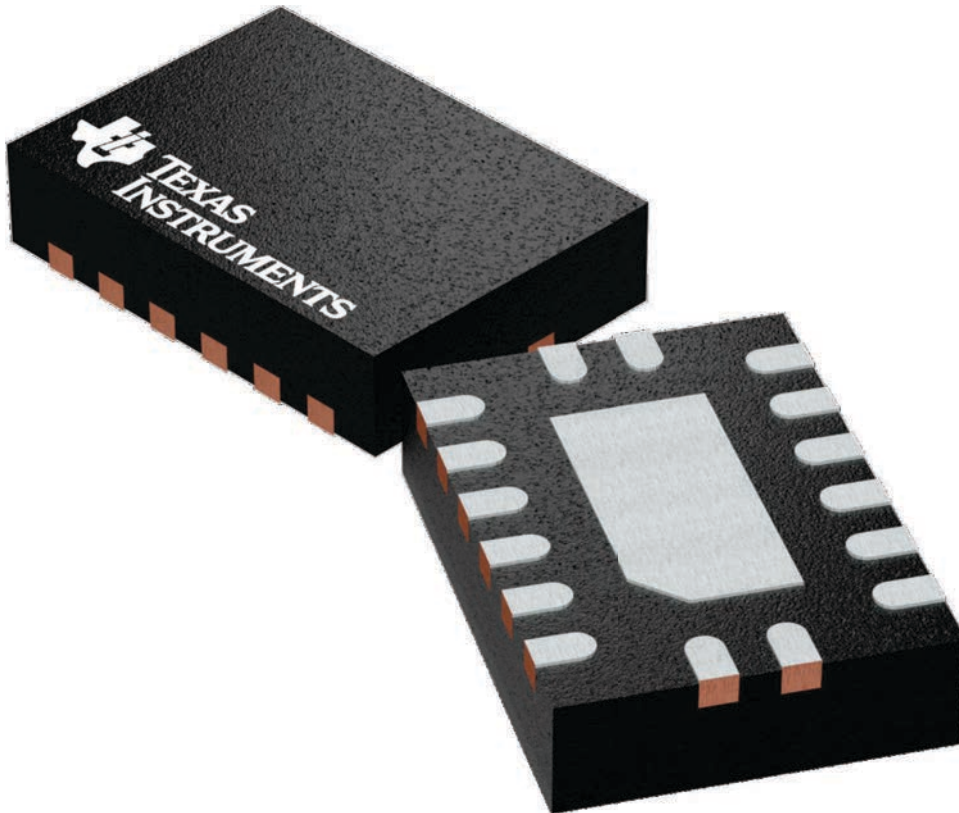
BQB 16

WQFN - 0.8 mm max height

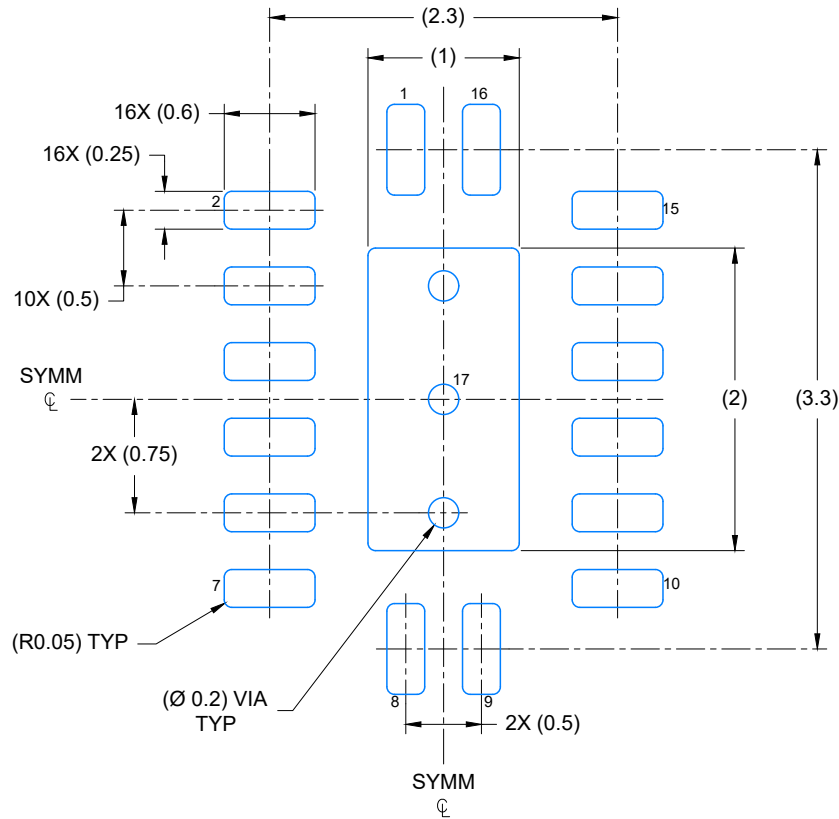
2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4226161/A

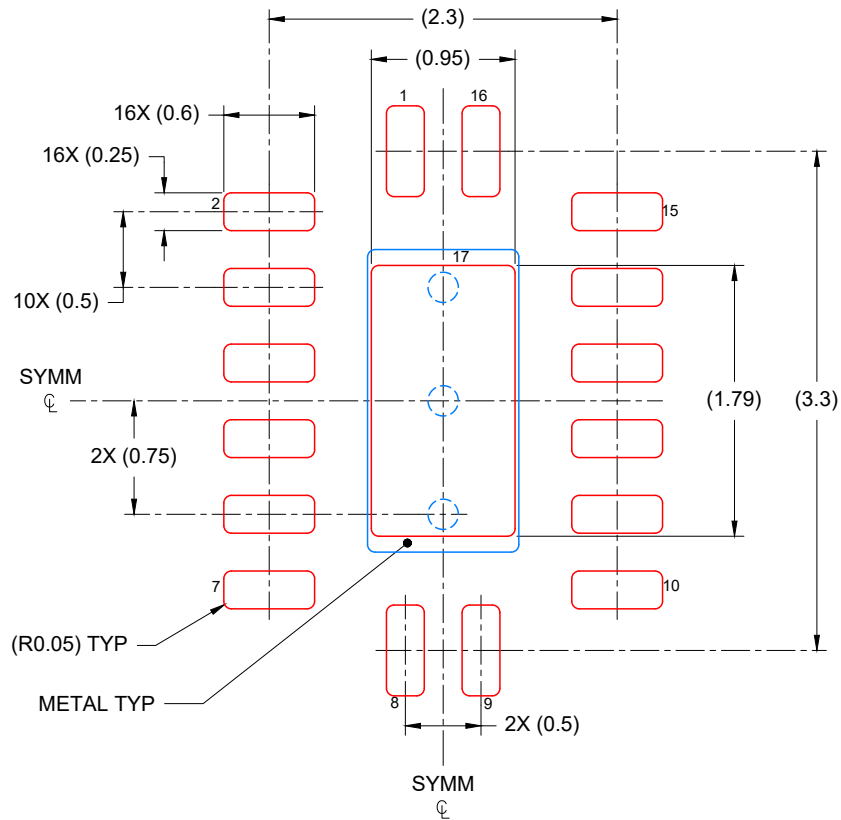


LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
 BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
 85% PRINTED COVERAGE BY AREA
 SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

重要声明和免责声明

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